



Silicon Tuning Varactors

Abrupt junction devices of planar epitaxial construction, intended for electronic tuning and other frequency control applications in the VHF/UHF ranges. Device performance has been optimised by careful attention to processing techniques. The use of oxide/nitride passivation produces varactors with good stability and low leakage.

Low substrate resistance and optimised metal contact schemes help to minimise series resistance, resulting in high values of Q.

Type	Total capacitance at 1 MHz (pF $\pm 10\%$)	Minimum capacitance ratio at 1 MHz	Minimum breakdown voltage at 10 μ A reverse current (V)	Minimum quality factor at 4 V, 50 MHz (Q)	Outline (see page 13)
DC4212B	10 at 4 V	3.0 at 4-60 V	60	350	07
DC4213B	12 at 4 V	3.0 at 4-60 V	60	350	07
DC4214B	15 at 4 V	3.1 at 4-60 V	60	300	07
DC4215B	18 at 4 V	3.1 at 4-60 V	60	250	07
DC4216B	22 at 4 V	3.2 at 4-60 V	60	250	07
DC4217B	27 at 4 V	3.2 at 4-60 V	60	200	07
DC4218B	33 at 4 V	3.2 at 4-60 V	60	200	07
DC4224B	39 at 4 V	3.2 at 4-60 V	60	200	07
DC4225B	47 at 4 V	3.2 at 4-60 V	60	200	07
DC4226B	56 at 4 V	3.2 at 4-60 V	60	120	14
DC4227B	68 at 4 V	3.2 at 4-60 V	60	120	14
DC4228	57 at 8 V	3.85 at 4-85 V	100	110	14
DC4229	57 at 8 V	3.85 at 4-85 V	100	125	14
DC4229D	57 at 8 V	3.85 at 4-85 V	100	200	14
DC4298	200 at 4 V	3.2 at 4-60 V	100	200	10
DC4299	335 at 4 V	3.2 at 4-60 V	100	200	10